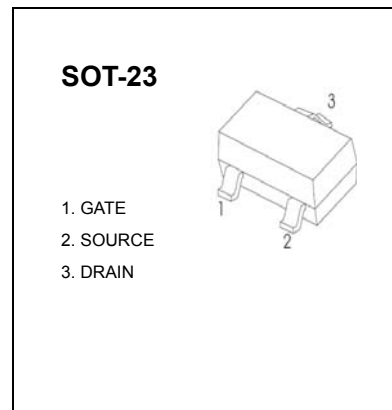


SOT-23 Plastic-Encapsulate MOSFETS

2N7002 MOSFET (N-Channel)

| $V_{(BR)DSS}$ | $R_{DS(on)MAX}$ | I_D |
|---------------|-----------------|-------|
| 60V | 5Ω@10V | 115mA |
| | 7Ω@5V | |



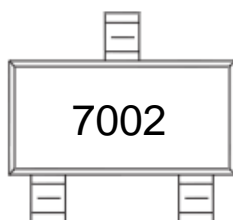
FEATURE

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

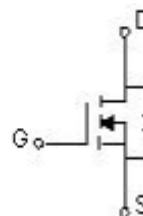
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|-----------------|-----------|---------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | 20 | V |
| Continuous Drain Current | I_D | 0.115 | A |
| Power Dissipation | P_D | 0.225 | W |
| Thermal Resistance from Junction to Ambient | $R_{\theta JA}$ | 556 | $^{\circ}C/W$ |
| Junction Temperature | T_J | 150 | $^{\circ}C$ |
| Storage Temperature | T_{stg} | -50 ~+150 | |

SOT-23 Plastic-Encapsulate MOSFETS

T_a=25 °C unless otherwise specified

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|---------------------------------|----------------------|---|------|-----|-------|------|
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} =0 V, I _D =250 μA | 60 | | | V |
| Gate-Threshold Voltage | V _{th(GS)} | V _{DS} =V _{GS} , I _D =250 μA | 1 | | 2.5 | |
| Gate-body Leakage | I _{GSS} | V _{DS} =0 V, V _{GS} =±20 V | | | ±80 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =60 V, V _{GS} =0 V | | | 80 | nA |
| On-state Drain Current | I _{D(ON)} | V _{GS} =10 V, V _{DS} =7 V | 500 | | | mA |
| Drain-Source On-Resistance | R _{DS(on)} | V _{GS} =10 V, I _D =500mA | | | 5 | Ω |
| | | V _{GS} =5 V, I _D =50mA | | | 7 | |
| Forward Trans conductance | g _{fs} | V _{DS} =10 V, I _D =200mA | 80 | | | ms |
| Drain-source on-voltage | V _{DS(on)} | V _{GS} =10V, I _D =500mA | | | 3.75 | V |
| | | V _{GS} =5V, I _D =50mA | | | 0.375 | V |
| Diode Forward Voltage | V _{SD} | I _S =115mA, V _{GS} =0 V | 0.55 | | 1.2 | V |
| Input Capacitance * | C _{iss} | V _{DS} =25V, V _{GS} =0V, f=1MHz | | | 50 | pF |
| Output Capacitance * | C _{oss} | | | | 25 | |
| Reverse Transfer Capacitance * | C _{rss} | | | | 5 | |

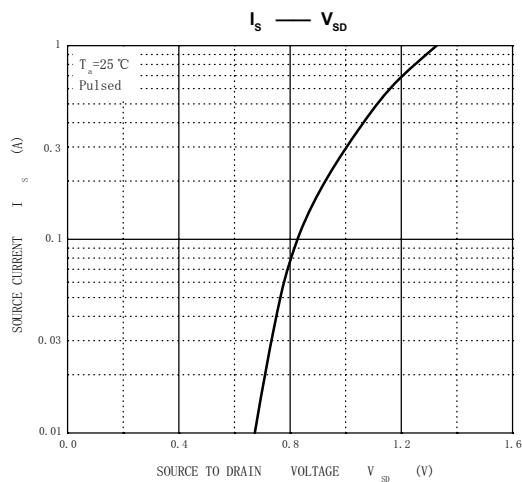
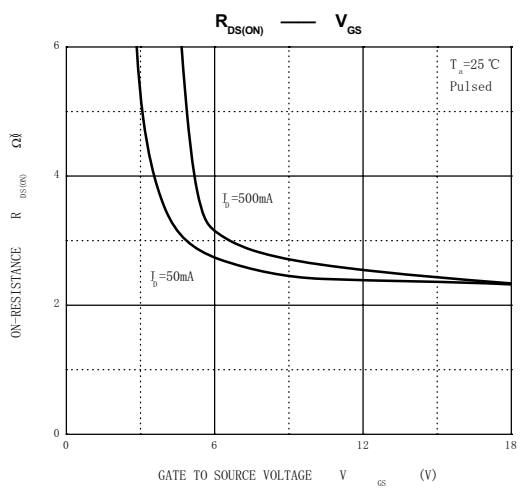
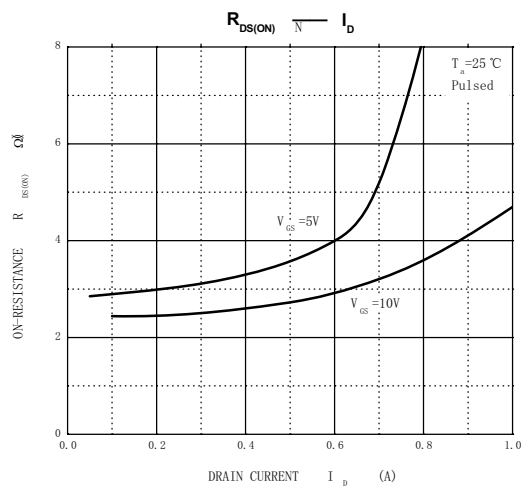
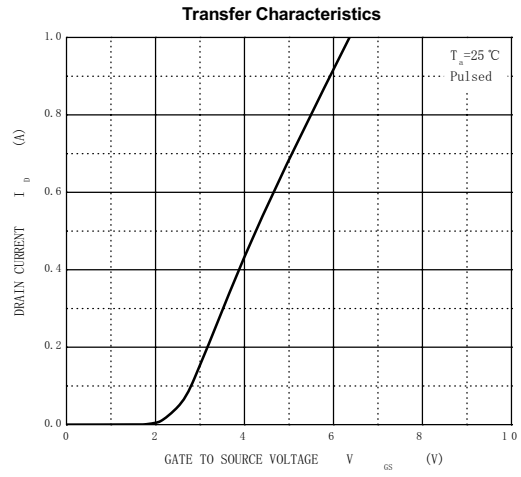
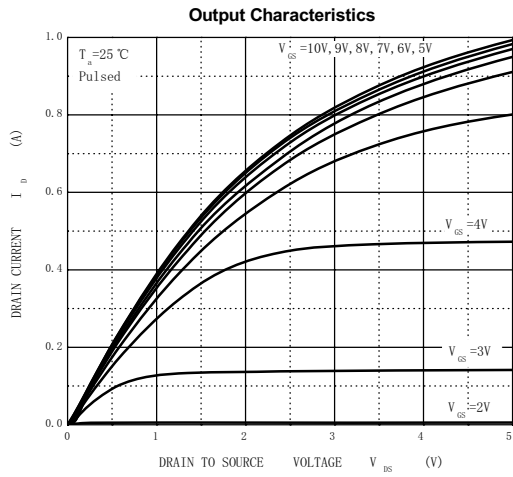
SWITCHING TIME

| | | | | | | |
|-----------------|---------------------|--|--|--|----|----|
| Turn-on Time * | t _{d(on)} | V _{DD} =25 V, R _L =50Ω, I _D =500mA, V _{GEN} =10 V | | | 20 | ns |
| Turn-off Time * | t _{d(off)} | R _G =25Ω | | | 40 | |

*These parameters have no way to verify.

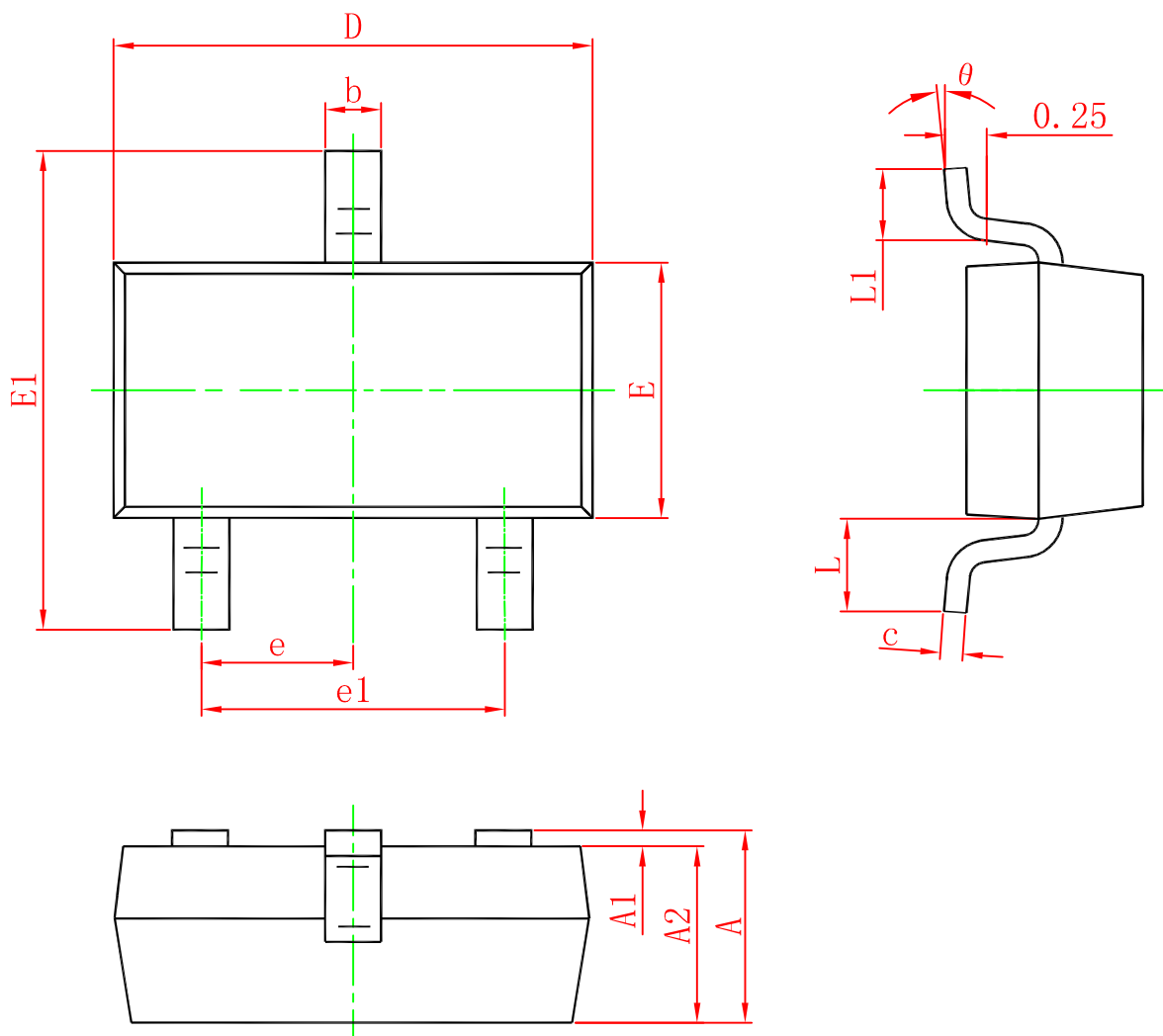
SOT-23 Plastic-Encapsulate MOSFETS

Typical Characteristics



SOT-23 Plastic-Encapsulate MOSFETS

SOT-23 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP. | | 0.037 TYP. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF. | | 0.022 REF. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |